

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 244683US2S	SERIAL NO. 10/695,857 New Application		
LIST OF REFERENCES CITED BY APPLICANT		APPLICANT Kenji TSUCHIDA					
		FILING DATE Herewith		GROUP 2829			
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>Tran</i>	AA	6,356,477	03/12/02	Lung T. TRAN			
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION		
	AO				YES	NO	
	AP						
	AQ						
	AR						
	AS						
	AT						
	AU						
	AV						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
<i>Tran</i>	AW	Roy SCHEUERLEIN, et al., "A 10ns Read and Write Non-Volatile Memory Array Using a Magnetic Tunnel Junction and FET Switch in each Cell", ISSCC 2000 DIGEST OF TECHINICAL PAPER, INTERNATIONAL SOLID-STATE CIRCUITS CONFERENCE, SESSION 7 / TD: EMERGING MEMORY & DEVICE TECHNOLOGIES, February 8, 2000, pgs. 128-129					
<i>Tran</i>	AX	Takeshi HONDA, et al., "MRAM-Writing Circuitry to Compensate for Thermal-Variation of Magnetization-Reversal Current", 2002 SYMPOSIUM ON VLSI CIRCUITS DIGEST OF TECHNICAL PAPERS, 2002, 1 page					
	AY						
	AZ				<input type="checkbox"/> Additional References sheet(s) attached		
Examiner	<i>Tuan T. Nguyen</i>			Date Considered 1/7/05			
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							